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教師研究成果資料明細

研究計畫

1.許健 其他單位 2008.05.1 ~2009.04.31
與世界先進積體電路股份有限公司產學合作

2.許健 其他單位 2009.05.1 ~2009.07.31
與世界先進積體電路股份有限公司產學合作

3.許健 其他單位 2010.09.1 ~2012.08.31
臺灣積體電路有限公司委託研究

4.許健 其他單位 2011.09.1 ~2013.08.31
新唐科技委託研究

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